

ABSTRACT

A plasma chamber comprising a lower electrode and an upper electrode, and used for dry-etching an LCD, comprises a main power supply comprising a main power source to generate a main voltage having a predetermined main frequency, and a first impedance matching circuit to impedance-match the main voltage; a bias power supply comprising a bias power source to generate a bias voltage having a predetermined bias frequency, and a second impedance matching circuit to impedance-match the bias voltage; and a mixer connected to both the first impedance matching circuit and the second impedance matching circuit, receiving and mixing the main voltage and the bias voltage, and outputting the mixed voltage to one of the lower electrode and the upper electrode. With this configuration, the present invention provides a plasma chamber in which etching conditions such as an etching rate, an etching profile, a selection ratio, etc. are precisely adjusted.